Hideo Hosono

List of Publications by Year
in descending order

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1,240	88,712	553	601
papers	citations	126 h-index	260 g-index

1325	1325	1325	35413
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Iron-Based Layered Superconductor La[O₁₋_xF_x]FeAs (x = 0.05â”0.12) with T_c = 26 K. Journal of the American Chemical Society, 2008, 130, 3296-3297.	6.6	7,243
2	Room-temperature fabrication of transparent flexible thin-film transistors using amorphous oxide semiconductors. Nature, 2004, 432, 488-492.	13.7	6,503
3	P-type electrical conduction in transparent thin films of CuAlO2. Nature, 1997, 389, 939-942.	13.7	1,896
4	Thin-Film Transistor Fabricated in Single-Crystalline Transparent Oxide Semiconductor. Science, 2003, 300, 1269-1272.	6.0	1,709
5	Present status of amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors. Science and Technology of Advanced Materials, 2010, 11, 044305.	2.8	1,559
6	Iron-Based Layered Superconductor:Â LaOFeP. Journal of the American Chemical Society, 2006, 128, 10012-10013.	6.6	1,207
7	Superconductivity at 43â€‰K in an iron-based layered compound LaO1-xFxFeAs. Nature, 2008, 453, 376-378.	13.7	1,139
8	Ammonia synthesis using a stable electride as an electron donor and reversible hydrogen store. Nature Chemistry, 2012, 4, 934-940.	6.6	1,085
9	High-mobility thin-film transistor with amorphous InGaZnO4 channel fabricated by room temperature rf-magnetron sputtering. Applied Physics Letters, 2006, 89, 112123.	1.5	1,048
10	Giant thermoelectric Seebeck coefficient of a two-dimensional electron gas in SrTiO3. Nature Materials, 2007, 6, 129-134.	13.3	910
11	Material characteristics and applications of transparent amorphous oxide semiconductors. NPG Asia Materials, 2010, 2, 15-22.	3.8	852
12	Deep-ultraviolet transparent conductive Î²-Ga2O3 thin films. Applied Physics Letters, 2000, 77, 4166-4168.	1.5	829
13	Ionic amorphous oxide semiconductors: Material design, carrier transport, and device application. Journal of Non-Crystalline Solids, 2006, 352, 851-858.	1.5	811
14	Transparent Conducting Oxides for Photovoltaics. MRS Bulletin, 2007, 32, 242-247.	1.7	788
15	High-Density Electron Anions in a Nanoporous Single Crystal: [Ca24Al28O64]4+(4e-). Science, 2003, 301, 626-629.	6.0	744
16	To What Extent Iron-Pnictide New Superconductors Have Been Clarified: A Progress Report. Journal of the Physical Society of Japan, 2009, 78, 062001.	0.7	682
17	Amorphous Oxide Semiconductors for High-Performance Flexible Thin-Film Transistors. Japanese Journal of Applied Physics, 2006, 45, 4303-4308.	0.8	659
18	p -channel thin-film transistor using p-type oxide semiconductor, SnO. Applied Physics Letters, 2008, 93, .	1.5	577

#	Article	IF	Citations
19	Recent progress in transparent oxide semiconductors: Materials and device application. Thin Solid Films, 2007, 515, 6000-6014.	0.8	567
20	Synthesis and control of conductivity of ultraviolet transmitting Î²-Ga2O3 single crystals. Applied Physics Letters, 1997, 70, 3561-3563.	1.5	539
21	Current injection emission from a transparent pâ€“n junction composed of p-SrCu2O2/n-ZnO. Applied Physics Letters, 2000, 77, 475-477.	1.5	539
22	Transparent p-Type Conducting Oxides: Design and Fabrication of p-n Heterojunctions. MRS Bulletin, 2000, 25, 28-36.	1.7	530
23	Electride support boosts nitrogen dissociation over ruthenium catalyst and shifts the bottleneck in ammonia synthesis. Nature Communications, 2015, 6, 6731.	5.8	529
24	Leadâ€Free Highly Efficient Blueâ€Emitting Cs₃Cu₂I₅ with 0D Electronic Structure. Advanced Materials, 2018, 30, e1804547.	11.1	477
25	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping. Journal of Display Technology, 2009, 5, 273-288.	1.3	464
26	Light-induced conversion of an insulating refractory oxide into a persistent electronic conductor. Nature, 2002, 419, 462-465.	13.7	431
27	Carrier transport and electronic structure in amorphous oxide semiconductor, a-InGaZnO4. Thin Solid Films, 2005, 486, 38-41.	0.8	423
28	Electronic structure and optoelectronic properties of transparent p-type conducting CuAlO[sub 2]. Journal of Applied Physics, 2000, 88, 4159.	1.1	413
29	Epitaxial growth of transparent p-type conducting CuGaO[sub 2] thin films on sapphire (001) substrates by pulsed laser deposition. Journal of Applied Physics, 2001, 89, 1790.	1.1	390
30	Dicalcium nitride as a two-dimensional electride with an anionic electron layer. Nature, 2013, 494, 336-340.	13.7	386
31	SrCu2O2: A p-type conductive oxide with wide band gap. Applied Physics Letters, 1998, 73, 220-222.	1.5	378
32	Highly Efficient Blueâ€Emitting Biâ€Doped Cs₂SnCl₆ Perovskite Variant: Photoluminescence Induced by Impurity Doping. Advanced Functional Materials, 2018, 28, 1801131.	7.8	358
33	Bipolarity in electrical conduction of transparent oxide semiconductor CuInO2 with delafossite structure. Applied Physics Letters, 2001, 78, 1583-1585.	1.5	332
34	Fabrication and photoresponse of a pn-heterojunction diode composed of transparent oxide semiconductors, p-NiO and n-ZnO. Applied Physics Letters, 2003, 83, 1029-1031.	1.5	329
35	Iron-based superconductors: Current status of materials and pairing mechanism. Physica C: Superconductivity and Its Applications, 2015, 514, 399-422.	0.6	326
36	Nature and origin of the 5-eV band inSiO2:GeO2glasses. Physical Review B, 1992, 46, 11445-11451.	1.1	325

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37	Large thermoelectric performance of heavily Nb-doped SrTiO3 epitaxial film at high temperature. Applied Physics Letters, 2005, 87, 092108.	1.5	324
38	Origins of threshold voltage shifts in room-temperature deposited and annealed a-Inâ€“Gaâ€“Znâ€“O thin-film transistors. Applied Physics Letters, 2009, 95, .	1.5	324
39	Anisotropy of electrical and optical properties in Î²-Ga2O3 single crystals. Applied Physics Letters, 1997, 71, 933-935.	1.5	323
40	Photocatalytic TiO2 thin film deposited onto glass by DC magnetron sputtering. Thin Solid Films, 2001, 392, 338-344.	0.8	318
41	Modeling of amorphous InGaZnO4 thin film transistors and their subgap density of states. Applied Physics Letters, 2008, 92, .	1.5	318
42	Transparent oxide optoelectronics. Materials Today, 2004, 7, 42-51.	8.3	310
43	Recent advances in iron-based superconductors toward applications. Materials Today, 2018, 21, 278-302.	8.3	310
44	Vacancy-enabled N2 activation for ammonia synthesis on an Ni-loaded catalyst. Nature, 2020, 583, 391-395.	13.7	309
45	Transparent p-type semiconductor: LaCuOS layered oxysulfide. Applied Physics Letters, 2000, 77, 2701-2703.	1.5	307
46	A novel phosphor for glareless white light-emitting diodes. Nature Communications, 2012, 3, 1132.	5.8	306
47	Evolution from Itinerant Antiferromagnet to Unconventional Superconductor with Fluorine Doping in LaFeAs(O_{1-x}F_x) Revealed by ⁷⁵As and ¹³⁹La Nuclear Magnetic Resonance. Journal of the Physical Society of Japan, 2008, 77, 073701.	0.7	303
48	Subgap states in transparent amorphous oxide semiconductor, Inâ€“Gaâ€“Znâ€“O, observed by bulk sensitive x-ray photoelectron spectroscopy. Applied Physics Letters, 2008, 92, .	1.5	298
49	Trap densities in amorphous-InGaZnO4 thin-film transistors. Applied Physics Letters, 2008, 92, .	1.5	290
50	Defect passivation and homogenization of amorphous oxide thin-film transistor by wet O2 annealing. Applied Physics Letters, 2008, 93, .	1.5	276
51	Local coordination structure and electronic structure of the large electron mobility amorphous oxide semiconductor In-Ga-Zn-O: Experiment andab initiocalculations. Physical Review B, 2007, 75, .	1.1	275
52	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping*. Journal of Display Technology, 2009, 5, 468-483.	1.3	272
53	Nickel-Based Oxyphosphide Superconductor with a Layered Crystal Structure, LaNiOP. Inorganic Chemistry, 2007, 46, 7719-7721.	1.9	268
54	Two types of oxygen-deficient centers in synthetic silica glass. Physical Review B, 1988, 38, 12772-12775.	1.1	263

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55	Preparation of highly conductive, deep ultraviolet transparent Î²-Ga2O3 thin film at low deposition temperatures. Thin Solid Films, 2002, 411, 134-139.	0.8	261
56	Highly electrically conductive indiumâ€“tinâ€“oxide thin films epitaxially grown on yttria-stabilized zirconia (100) by pulsed-laser deposition. Applied Physics Letters, 2000, 76, 2740-2742.	1.5	259
57	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides MCuOCh (M = Bi, La; Ch = S, Se, Te): Effects of Electronic Configurations of M³⁺ Ions. Chemistry of Materials, 2008, 20, 326-334.	3.2	258
58	Carrier transport in transparent oxide semiconductor with intrinsic structural randomness probed using single-crystalline InGaO3(ZnO)5 films. Applied Physics Letters, 2004, 85, 1993-1995.	1.5	247
59	Advantageous grain boundaries in iron pnictide superconductors. Nature Communications, 2011, 2, 409.	5.8	246
60	Novel oxide amorphous semiconductors: transparent conducting amorphous oxides. Journal of Non-Crystalline Solids, 1996, 203, 334-344.	1.5	238
61	Ambipolar Oxide Thinâ€Film Transistor. Advanced Materials, 2011, 23, 3431-3434.	11.1	236
62	Crystallographic phase transition and high-T_csuperconductivity in LaFeAsO:F. Superconductor Science and Technology, 2008, 21, 125028.	1.8	230
63	Microporous Crystal 12CaOÂ·7Al2O3 Encaging Abundant O- Radicals. Journal of the American Chemical Society, 2002, 124, 738-739.	6.6	225
64	Epitaxial growth of high mobility Cu2O thin films and application to p-channel thin film transistor. Applied Physics Letters, 2008, 93, .	1.5	222
65	Ternary intermetallic LaCoSi as a catalyst for N2 activation. Nature Catalysis, 2018, 1, 178-185.	16.1	221
66	Combinatorial approach to thin-film transistors using multicomponent semiconductor channels: An application to amorphous oxide semiconductors in Inâ€“Gaâ€“Znâ€“O system. Applied Physics Letters, 2007, 90, 242114.	1.5	219
67	Electronic Structures Above Mobility Edges in Crystalline and Amorphous In-Ga-Zn-O: Percolation Conduction Examined by Analytical Model. Journal of Display Technology, 2009, 5, 462-467.	1.3	219
68	Water Durable Electride Y₅Si₃: Electronic Structure and Catalytic Activity for Ammonia Synthesis. Journal of the American Chemical Society, 2016, 138, 3970-3973.	6.6	217
69	Electronic structure of oxygen deficient amorphous oxide semiconductor aâ€InGaZnO_{4â€“x}: Optical analyses and firstâ€principle calculations. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3098-3100.	0.8	214
70	Tin monoxide as an sâ€orbitalâ€based pâ€type oxide semiconductor: Electronic structures and TFT application. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2187-2191.	0.8	213
71	Work Function of a Roomâ€Temperature, Stable Electride [Ca₂₄Al₂₈O₆₄]⁴⁺(e^{â€“})₄. Advanced Materials, 2007, 19, 3564-3569.	11.1	209
72	Metallic State in a Limeâ€'Alumina Compound with Nanoporous Structure. Nano Letters, 2007, 7, 1138-1143.	4.5	208

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73	Discovery of earth-abundant nitride semiconductors by computational screening and high-pressure synthesis. Nature Communications, 2016, 7, 11962.	5.8	208
74	Electronic structure of the amorphous oxide semiconductor aâ€InGaZnO_{4â€“x}: Taucâ€“Lorentz optical model and origins of subgap states. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 860-867.	0.8	207
75	UV-detector based on pn-heterojunction diode composed of transparent oxide semiconductors, p-NiO/n-ZnO. Thin Solid Films, 2003, 445, 317-321.	0.8	206
76	Effects of excess oxygen on operation characteristics of amorphous In-Ga-Zn-O thin-film transistors. Applied Physics Letters, 2011, 99, .	1.5	203
77	Band-gap widening of CdO thin films. Journal of Applied Physics, 1998, 84, 6174-6177.	1.1	202
78	Superconductivity in an Inorganic Electride 12CaOÂ·7Al2O3:e-. Journal of the American Chemical Society, 2007, 129, 7270-7271.	6.6	199
79	Working hypothesis to explore novel wide band gap electrically conducting amorphous oxides and examples. Journal of Non-Crystalline Solids, 1996, 198-200, 165-169.	1.5	198
80	Two-dome structure in electron-doped iron arsenide superconductors. Nature Communications, 2012, 3, 943.	5.8	198
81	Superconductivity Induced by Co-Doping in Quaternary Fluoroarsenide CaFeAsF. Journal of the American Chemical Society, 2008, 130, 14428-14429.	6.6	197
82	Essential role of hydride ion in ruthenium-based ammonia synthesis catalysts. Chemical Science, 2016, 7, 4036-4043.	3.7	195
83	Fabrication of transparent pâ€n heterojunction thin film diodes based entirely on oxide semiconductors. Applied Physics Letters, 1999, 75, 2851-2853.	1.5	194
84	Natural van der Waals heterostructural single crystals with both magnetic and topological properties. Science Advances, 2019, 5, eaax9989.	4.7	193
85	Electron Localization and a Confined Electron Gas in Nanoporous Inorganic Electrides. Physical Review Letters, 2003, 91, 126401.	2.9	192
86	Specific contact resistances between amorphous oxide semiconductor Inâ€Gaâ€Znâ€O and metallic electrodes. Thin Solid Films, 2008, 516, 5899-5902.	0.8	191
87	Effects of Diffusion of Hydrogen and Oxygen on Electrical Properties of Amorphous Oxide Semiconductor, In-Ga-Zn-O. ECS Journal of Solid State Science and Technology, 2013, 2, P5-P8.	0.9	191
88	Intrinsic defects in a photovoltaic perovskite variant Cs₂SnI₆. Physical Chemistry Chemical Physics, 2015, 17, 18900-18903.	1.3	191
89	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. Applied Physics Letters, 2010, 97, .	1.5	189
90	Exploration of new superconductors and functional materials, and fabrication of superconducting tapes and wires of iron pnictides. Science and Technology of Advanced Materials, 2015, 16, 033503.	2.8	188

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91	Amorphous IGZO TFT with High Mobility of â^¼470 cm²/(V s) via Vertical Dimension Control Using PEALD. ACS Applied Materials & Interfaces, 2019, 11, 40300-40309.	4.0	188
92	Single-Crystalline Films of the Homologous Series InGaO3(ZnO)m Grown by Reactive Solid-Phase Epitaxy. Advanced Functional Materials, 2003, 13, 139-144.	7.8	179
93	Electronic Defects in Amorphous Oxide Semiconductors: A Review. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800372.	0.8	179
94	Field Emission of Electron Anions Clathrated in Subnanometer-Sized Cages in [Ca24Al28O64]4+(4e-). Advanced Materials, 2004, 16, 685-689.	11.1	175
95	Growth, structure and carrier transport properties of Ga2O3 epitaxial film examined for transparent field-effect transistor. Thin Solid Films, 2006, 496, 37-41.	0.8	173
96	Ru-Loaded C12A7:e^{â€“} Electride as a Catalyst for Ammonia Synthesis. ACS Catalysis, 2017, 7, 2313-2324.	5.5	173
97	Amorphous Inâ€“Gaâ€“Znâ€“O coplanar homojunction thin-film transistor. Applied Physics Letters, 2009, 94, 133502.	1.5	168
98	Twoâ€photon processes in defect formation by excimer lasers in synthetic silica glass. Applied Physics Letters, 1988, 53, 1891-1893.	1.5	167
99	Fabrication and characterization of ultraviolet-emitting diodes composed of transparent p-n heterojunction, p-SrCu2O2 and n-ZnO. Journal of Applied Physics, 2001, 89, 5720-5725.	1.1	166
100	Degenerate p-type conductivity in wide-gap LaCuOS1â^'xSex (x=0â€“1) epitaxial films. Applied Physics Letters, 2003, 82, 1048-1050.	1.5	166
101	Amorphous oxide channel TFTs. Thin Solid Films, 2008, 516, 1516-1522.	0.8	166
102	Occurrence of superoxide radical ion in crystalline calcium aluminate 12CaO.7Al2O3 prepared via solid-state reactions. Inorganic Chemistry, 1987, 26, 1192-1195.	1.9	164
103	Frontier of transparent conductive oxide thin films. Vacuum, 2002, 66, 419-425.	1.6	164
104	Superconductivity under High Pressure in LaFeAsO. Journal of the Physical Society of Japan, 2008, 77, 113712.	0.7	163
105	Factors controlling electron transport properties in transparent amorphous oxide semiconductors. Journal of Non-Crystalline Solids, 2008, 354, 2796-2800.	1.5	162
106	Discovery of hexagonal ternary phase Ti2InB2 and its evolution to layered boride TiB. Nature Communications, 2019, 10, 2284.	5.8	159
107	Formation and Characterization of Hydrogen Boride Sheets Derived from MgB₂ by Cation Exchange. Journal of the American Chemical Society, 2017, 139, 13761-13769.	6.6	157
108	Highly stable amorphous In-Ga-Zn-O thin-film transistors produced by eliminating deep subgap defects. Applied Physics Letters, 2011, 99, .	1.5	156

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109	A p-Type Amorphous Oxide Semiconductor and Room Temperature Fabrication of Amorphous Oxide pâ€“n Heterojunction Diodes. Advanced Materials, 2003, 15, 1409-1413.	11.1	154
110	A Possible Ground State and Its Electronic Structure of a Mother Material (LaOFeAs) of New Superconductors. Journal of the Physical Society of Japan, 2008, 77, 053709.	0.7	152
111	Depth analysis of subgap electronic states in amorphous oxide semiconductor, a-In-Ga-Zn-O, studied by hard x-ray photoelectron spectroscopy. Journal of Applied Physics, 2011, 109, 073726.	1.1	151
112	Activation and splitting of carbon dioxide on the surface of an inorganic electride material. Nature Communications, 2013, 4, 2378.	5.8	151
113	Two-Dimensional Transition-Metal Electride Y₂C. Chemistry of Materials, 2014, 26, 6638-6643.	3.2	151
114	Subgap states, doping and defect formation energies in amorphous oxide semiconductor aâ€InGaZnO₄ studied by density functional theory. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1698-1703.	0.8	149
115	Photochemical reactions inGeO2-SiO2glasses induced by ultraviolet irradiation: Comparison between Hg lamp and excimer laser. Physical Review B, 1995, 52, 1661-1665.	1.1	148
116	Bipolar Conduction in SnO Thin Films. Electrochemical and Solid-State Letters, 2011, 14, H13.	2.2	148
117	Ammonia decomposition by ruthenium nanoparticles loaded on inorganic electride C12A7:eâ^'. Chemical Science, 2013, 4, 3124.	3.7	148
118	Chemical Design and Thin Film Preparation of p-Type Conductive Transparent Oxides. , 2000, 4, 407-414.		144
119	Selfâ€organized Rutheniumâ€“Barium Coreâ€“Shell Nanoparticles on a Mesoporous Calcium Amide Matrix for Efficient Lowâ€Temperature Ammonia Synthesis. Angewandte Chemie - International Edition, 2018, 57, 2648-2652.	7.2	144
120	Physical Disorder and Optical Properties in the Vacuum Ultraviolet Region of AmorphousSiO2. Physical Review Letters, 2001, 87, 175501.	2.9	141
121	Mechano-catalytic overall water splitting. Chemical Communications, 1998, , 2185-2186.	2.2	139
122	Origin of definite Hall voltage and positive slope in mobility-donor density relation in disordered oxide semiconductors. Applied Physics Letters, 2010, 96, .	1.5	139
123	Experimental evidence for the Si-Si bond model of the 7.6-eV band inSiO2glass. Physical Review B, 1991, 44, 12043-12045.	1.1	138
124	Itinerant ferromagnetism in the layered crystals<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>LaCoO</mml:mtext><mml:mi>X</mml:mi><mml:mspace width="0.3em" /><mml:mo>(</mml:mo><mml:mrow><mml:mi>X</mml:mi><mml:mo>=</mml:mo><mml:mtext>P</mml:mtext><mml:mo	1.1	138
125	Physical Review B, 2008, 77, . Field-induced current modulation in epitaxial film of deep-ultraviolet transparent oxide semiconductor Ga2O3. Applied Physics Letters, 2006, 88, 092106.	1.5	137
126	Fabrication of all oxide transparent pâ€“n homojunction using bipolar CuInO2 semiconducting oxide with delafossite structure. Solid State Communications, 2001, 121, 15-17.	0.9	134

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127	Room-temperature excitons in wide-gap layered-oxysulfide semiconductor: LaCuOS. Applied Physics Letters, 2001, 78, 2333-2335.	1.5	133
128	Ligand-Hole in [SnI6] Unit and Origin of Band Gap in Photovoltaic Perovskite Variant Cs2SnI6. Bulletin of the Chemical Society of Japan, 2015, 88, 1250-1255.	2.0	130
129	Frontier of transparent oxide semiconductors. Solid-State Electronics, 2003, 47, 2261-2267.	0.8	129
130	Efficient and Stable Ammonia Synthesis by Self-Organized Flat Ru Nanoparticles on Calcium Amide. ACS Catalysis, 2016, 6, 7577-7584.	5.5	129
131	Solvated Electrons in High-Temperature Melts and Glasses of the Room-Temperature Stable Electride [Ca ₂₄ Al ₂₈ O ₆₄] ⁴⁺ â‹…4e ^{â^'}. Science, 2011, 333, 71-74.	6.0	127
132	Contribution of Nitrogen Vacancies to Ammonia Synthesis over Metal Nitride Catalysts. Journal of the American Chemical Society, 2020, 142, 14374-14383.	6.6	126
133	Advances in Materials and Applications of Inorganic Electrides. Chemical Reviews, 2021, 121, 3121-3185.	23.0	125
134	Crystal structure of metastable Î²-CeZrO4 phase possessing an ordered arrangement of Ce and Zr ions. Journal of Alloys and Compounds, 2000, 312, 94-103.	2.8	124
135	Circuits using uniform TFTs based on amorphous Inâ€Gaâ€Znâ€O. Journal of the Society for Information Display, 2007, 15, 915-921.	0.8	121
136	Hydrogen anion and subgap states in amorphous Inâ€“Gaâ€“Znâ€“O thin films for TFT applications. Applied Physics Letters, 2017, 110, .	1.5	121
137	Fabrication and characterization of heteroepitaxial p-n junction diode composed of wide-gap oxide semiconductors p-ZnRh2O4/n-ZnO. Applied Physics Letters, 2003, 82, 823-825.	1.5	119
138	Nickel-based phosphide superconductor with infinite-layer structure, BaNi2P2. Solid State Communications, 2008, 147, 111-113.	0.9	118
139	Surface morphology and crystal quality of low resistive indium tin oxide grown on yittria-stabilized zirconia. Journal of Applied Physics, 2002, 91, 3547-3550.	1.1	116
140	From Insulator to Electride:Â A Theoretical Model of Nanoporous Oxide 12CaOÂ·7Al2O3. Journal of the American Chemical Society, 2007, 129, 942-951.	6.6	115
141	Bipartite magnetic parent phases in the iron oxypnictide superconductor. Nature Physics, 2014, 10, 300-303.	6.5	115
142	Mobilityâ€“stability trade-off in oxide thin-film transistors. Nature Electronics, 2021, 4, 800-807.	13.1	115
143	Fabrication of surface relief gratings on transparent dielectric materials by two-beam holographic method using infrared femtosecond laser pulses. Applied Physics B: Lasers and Optics, 2000, 71, 119-121.	1.1	114
144	Electronic structure of the transparentp-type semiconductor (LaO)CuS. Physical Review B, 2001, 64, .	1.1	114

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145	Experimental Evidence for Frenkel Defect Formation in AmorphousSiO2by Electronic Excitation. Physical Review Letters, 1998, 80, 317-320.	2.9	113
146	Decomposition of water by a CaTiO3 photocatalyst under UV light irradiation. Materials Research Bulletin, 2002, 37, 2401-2406.	2.7	112
147	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. Applied Physics Letters, 2013, 103, .	1.5	112
148	Transparent amorphous oxide semiconductors for organic electronics: Application to inverted OLEDs. Proceedings of the National Academy of Sciences of the United States of America, 2017, 114, 233-238.	3.3	111
149	Fast Thin-Film Transistor Circuits Based on Amorphous Oxide Semiconductor. IEEE Electron Device Letters, 2007, 28, 273-275.	2.2	110
150	Biaxially textured cobalt-doped BaFe2As2 films with high critical current density over 1â€‚MA/cm2 on MgO-buffered metal-tape flexible substrates. Applied Physics Letters, 2011, 98, 242510.	1.5	110
151	Synthesis of a Room Temperature Stable 12CaOÂ·7Al2O3 Electride from the Melt and Its Application as an Electron Field Emitter. Chemistry of Materials, 2006, 18, 1938-1944.	3.2	109
152	Hydrogen in layered iron arsenides: Indirect electron doping to induce superconductivity. Physical Review B, 2011, 84, .	1.1	109
153	A Solutionâ€Processed Ultrafast Optical Switch Based on a Nanostructured Epsilonâ€Nearâ€Zero Medium. Advanced Materials, 2017, 29, 1700754.	11.1	109
154	Hydride ions in oxide hosts hidden by hydroxide ions. Nature Communications, 2014, 5, 3515.	5.8	108
155	Protonic conduction in oxide glasses: simple relations between electrical conductivity, activation energy, and the o-h bonding state. Physical Review B, 1988, 38, 10166-10169.	1.1	107
156	High-Throughput ab Initio Screening for Two-Dimensional Electride Materials. Inorganic Chemistry, 2014, 53, 10347-10358.	1.9	107
157	Low-Temperature Synthesis of Perovskite Oxynitride-Hydrides as Ammonia Synthesis Catalysts. Journal of the American Chemical Society, 2019, 141, 20344-20353.	6.6	106
158	Heteroepitaxial growth of a wide-gap p-type semiconductor, LaCuOS. Applied Physics Letters, 2002, 81, 598-600.	1.5	105
159	ZnRh2O4: A p-type semiconducting oxide with a valence band composed of a low spin state of Rh3+ in a 4d6 configuration. Applied Physics Letters, 2002, 80, 1207-1209.	1.5	105
160	Long lasting phosphorescence and photostimulated luminescence in Tb-ion-activated reduced calcium aluminate glasses. Journal of Applied Physics, 1999, 86, 3729-3733.	1.1	104
161	Pseudoisotropic Upper Critical Field in Cobalt-Doped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>SrFe</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>As</mml:mi><mml Films. Physical Review Letters, 2009, 102, 117004.	2.9	104
162	Intermetallic Electride Catalyst as a Platform for Ammonia Synthesis. Angewandte Chemie - International Edition, 2019, 58, 825-829.	7.2	104

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163	Superconductivity in Epitaxial Thin Films of Co-Doped SrFe2As2with Bilayered FeAs Structures and their Magnetic Anisotropy. Applied Physics Express, 2008, 1, 101702.	1.1	103
164	Bandgap Optimization of Perovskite Semiconductors for Photovoltaic Applications. Chemistry - A European Journal, 2018, 24, 2305-2316.	1.7	103
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